

## CMOS Expandable 4-Wide 2-Input AND-OR-INVERT Gate

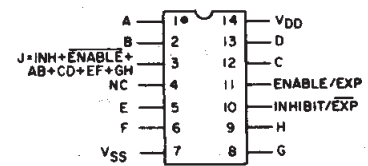
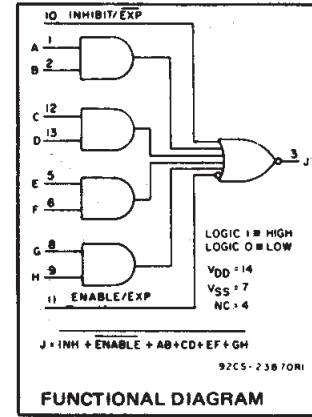
High-Voltage Types (20-Volt Rating)

■ CD4086B contains one 4-wide 2-input AND-OR-INVERT gate with an INHIBIT/EXP input and an ENABLE/EXP input. For a 4-wide A-O-I function INHIBIT/EXP is tied to V<sub>SS</sub> and ENABLE/EXP to V<sub>DD</sub>. See Fig.10 and its associated explanation for applications where a capability greater than 4-wide is required.

The CD4086B is supplied in 14-lead dual-in-line ceramic packages (D and F suffixes), 14-lead dual-in-line plastic packages (E suffix), and in chip form (H suffix).

### Features:

- Medium-speed operation – t<sub>PHL</sub> = 90 ns; t<sub>PLH</sub> = 140 ns (typ.) at 10 V
- INHIBIT and ENABLE inputs
- Buffered outputs
- 100% tested for quiescent current at 20 V
- Maximum input leakage current of 18 V over full package-temperature range; 100 nA at 18 V and 25°C
- Noise margin (over full package temperature range):
  - 1 V at V<sub>DD</sub> = 5 V
  - 2 V at V<sub>DD</sub> = 10 V
  - 2.5 V at V<sub>DD</sub> = 15 V
- Standardized, symmetrical output characteristics
- 5-V, 10-V, and 15-V parametric ratings
- Meets all requirements of JEDEC Tentative Standard No. 13B, "Standard Specifications for Description of 'B' Series CMOS Devices"



92CS-23869R1  
Top View  
TERMINAL ASSIGNMENT

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE RANGE, (V <sub>DD</sub> ) Voltages referenced to V <sub>SS</sub> Terminal)	-0.5V to +20V
INPUT VOLTAGE RANGE, ALL INPUTS	-0.5V to V <sub>DD</sub> + 0.5V
DC INPUT CURRENT, ANY ONE INPUT	±10mA
POWER DISSIPATION PER PACKAGE (P <sub>D</sub> ):	
For T <sub>A</sub> = -55°C to +100°C	500mW
For T <sub>A</sub> = +100°C to +125°C	Derate Linearly at 12mW/°C to 200mW
DEVICE DISSIPATION PER OUTPUT TRANSISTOR	
FOR T <sub>A</sub> = FULL PACKAGE-TEMPERATURE RANGE (All Package Types)	100mW
OPERATING-TEMPERATURE RANGE (T <sub>A</sub> )	-55°C to +125°C
STORAGE TEMPERATURE RANGE (T <sub>stg</sub> )	-65°C to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 ± 1/32 Inch (1.59 ± 0.79mm) from case for 10s max	+265°C

### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range (For T <sub>A</sub> = Full Package-Temperature Range)	3	18	V

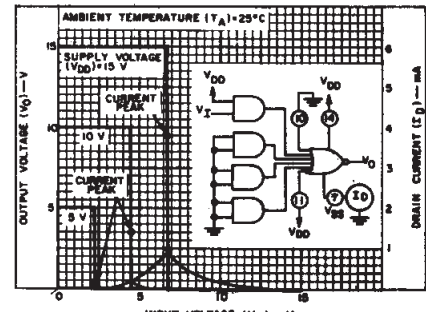


Fig. 1 – Typical voltage and current transfer characteristics.

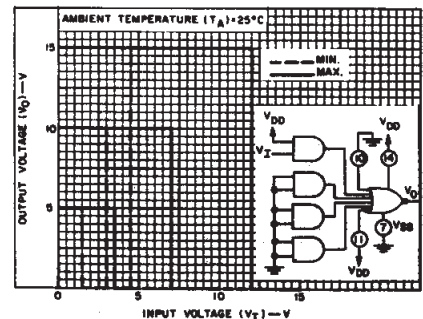


Fig. 2 – Minimum and maximum voltage transfer characteristics.

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# CD4086B Types

## STATIC ELECTRICAL CHARACTERISTICS

CHARACTERISTIC	CONDITIONS			LIMITS AT INDICATED TEMPERATURES (°C)							UNITS	
	V <sub>O</sub> (V)	V <sub>IN</sub> (V)	V <sub>DD</sub> (V)	-55	-40	+85	+125	+25				
								Min.	Typ.	Max.		
Quiescent Device Current I <sub>DD</sub> Max.	—	0.5	5	1	1	30	30	—	0.02	1	μA	
	—	0.10	10	2	2	60	60	—	0.02	2		
	—	0.15	15	4	4	120	120	—	0.02	4		
Output Low (Sink) Current, I <sub>OL</sub> Min.	0.4	0.5	5	0.64	0.61	0.42	0.36	0.51	1	—	mA	
	0.5	0.10	10	1.6	1.5	1.1	0.9	1.3	2.6	—		
	1.5	0.15	15	4.2	4	2.8	2.4	3.4	6.8	—		
Output High (Source) Current, I <sub>OH</sub> Min.	4.6	0.5	5	-0.64	-0.61	-0.42	-0.36	-0.51	-1	—	mA	
	2.5	0.5	5	-2	-1.8	-1.3	-1.15	-1.6	-3.2	—		
	9.5	0.10	10	-1.6	-1.5	-1.1	-0.9	-1.3	-2.6	—		
Output Voltage: Low-Level, V <sub>OL</sub> Max.	—	0.5	5	0.05			—			0	0.05	V
	—	0.10	10	0.05			—			0	0.05	
	—	0.15	15	0.05			—			0	0.05	
Output Voltage: High-Level, V <sub>OH</sub> Min.	—	0.5	5	4.95			4.95			5	—	V
	—	0.10	10	9.95			9.95			10	—	
	—	0.15	15	14.95			14.95			15	—	
Input Low Voltage, V <sub>IL</sub> Max.	0.5, 4.5	—	5	1.5			—			1.5	V	
	1.9	—	10	3			—			3		
	1.5, 13.5	—	15	4			—			4		
Input High Voltage, V <sub>IH</sub> Min.	0.5, 4.5	—	5	3.5			3.5			—	V	
	1.9	—	10	7			7			—		
	1.5, 13.5	—	15	11			11			—		
Input Current, I <sub>IN</sub> Max.	—	0.18	18	±0.1	±0.1	±1	±1	—	±10 <sup>-5</sup>	±0.1	μA	

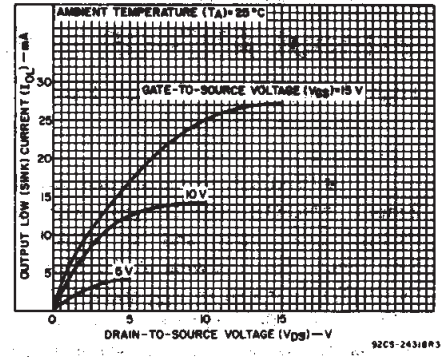


Fig. 3 — Typical output low (sink) current characteristics.

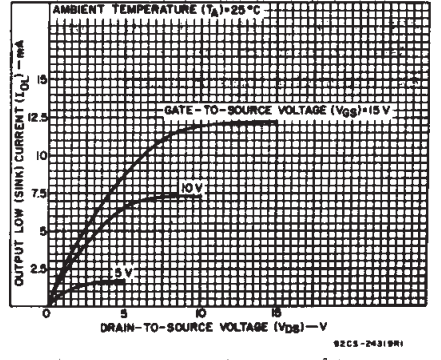


Fig. 4 — Minimum output low (sink) current characteristics.

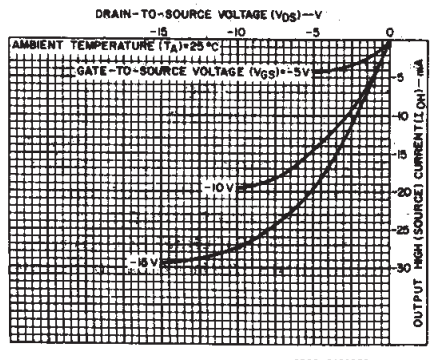


Fig. 5 — Typical output high (source) current characteristics.

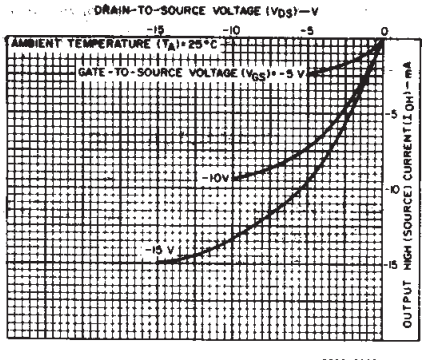


Fig. 8 — Minimum output high (source) current characteristics.

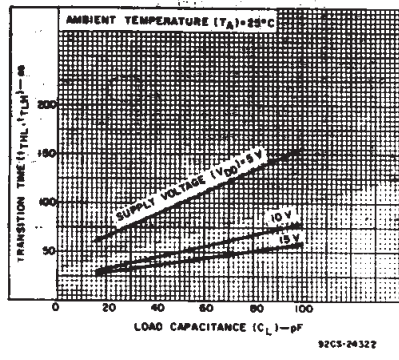


Fig. 6 — Typical transition time vs. load capacitance.

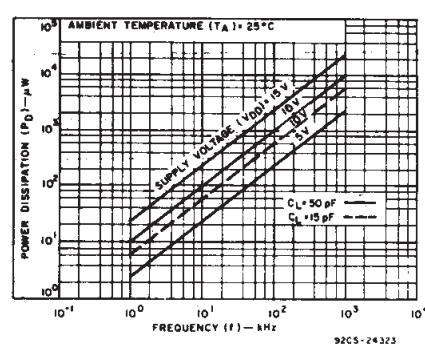


Fig. 7 — Typical power dissipation vs. frequency.

# CD4086B Types

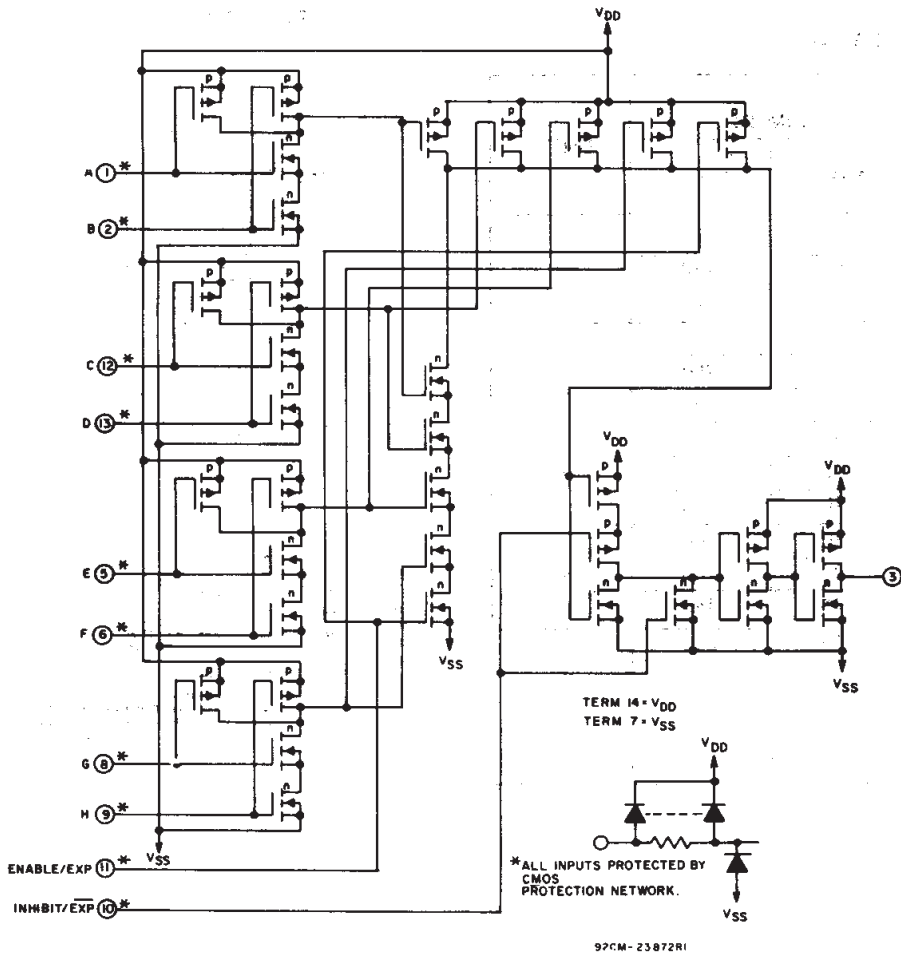


Fig. 9 - CD4086B schematic diagram.

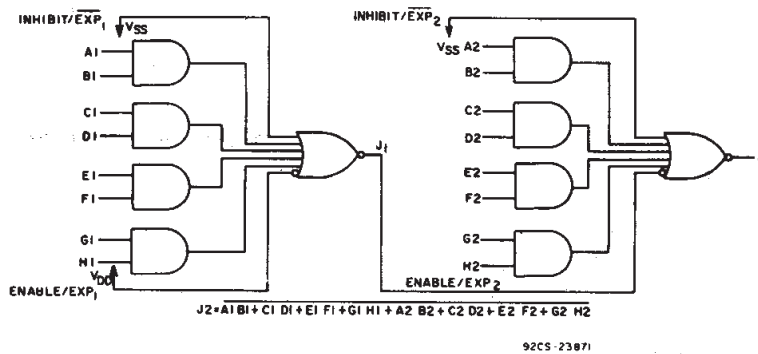


Fig. 10 - Two CD4086's connected as an 8-wide 2-input A-O-I gate.

Fig. 10 above shows two CD4086's utilized to obtain an 8-wide 2-input A-O-I function. The output (J1) of one CD4086 is fed directly to the ENABLE/EXP2 line of the second CD4086. In a similar fashion, any

NAND gate output can be fed directly into the ENABLE/EXP input to obtain a 5-wide A-O-I function. In addition, any AND gate output can be fed directly into the INHIBIT/EXP input with the same result.

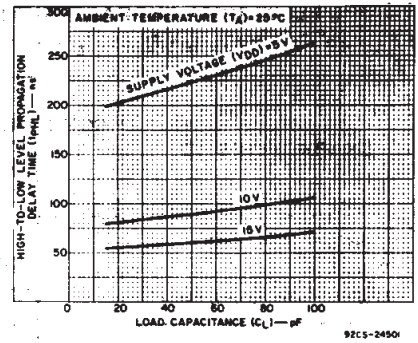


Fig. 11 - Typical DATA or ENABLE high-to-low level propagation delay time vs. load capacitance.

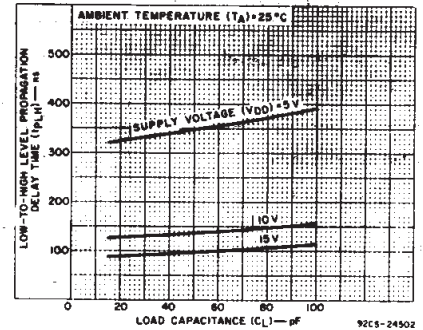


Fig. 12 - Typical DATA or ENABLE low-to-high level propagation delay time vs. load capacitance.

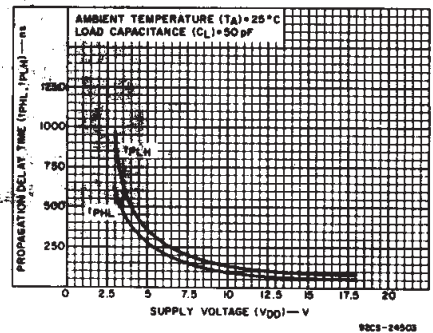


Fig. 13 - Typical DATA or ENABLE propagation delay time vs. supply voltage.

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# CD4086B Types

## DYNAMIC ELECTRICAL CHARACTERISTICS

At  $T_A = 25^\circ\text{C}$ ; Input  $t_r, t_f = 20\text{ ns}$ ,  $C_L = 50\text{ pF}$ ,  $R_L = 200\text{ k}\Omega$

CHARACTERISTIC	CONDITIONS	LIMITS		UNITS	
		$V_{DD}$ (V)	TYP.		MAX.
Propagation Delay Time (Data): High-to-Low Level, $t_{pHL}$		5	225	450	ns
		10	90	180	
		15	60	120	
Low-to-High Level, $t_{pLH}$		5	310	620	ns
		10	125	250	
		15	90	180	
Propagation Delay Time (Inhibit): High-to-Low Level, $t_{pHL(INH)}$		5	150	300	ns
		10	60	120	
		15	40	80	
Low-to-High Level, $t_{pLH(INH)}$		5	250	500	ns
		10	100	200	
		15	70	140	
Transition Time, $t_{THL}, t_{TLH}$		5	100	200	ns
		10	50	100	
		15	40	80	
Input Capacitance $C_{iN}$	Any Input		5	7.5	pF

## TEST CIRCUITS

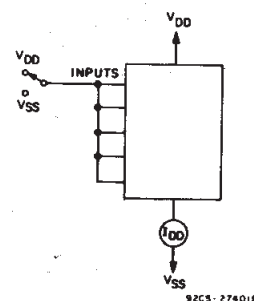


Fig. 14 - Quiescent device current.

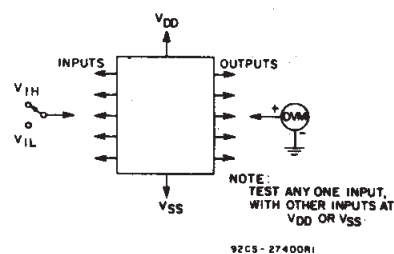
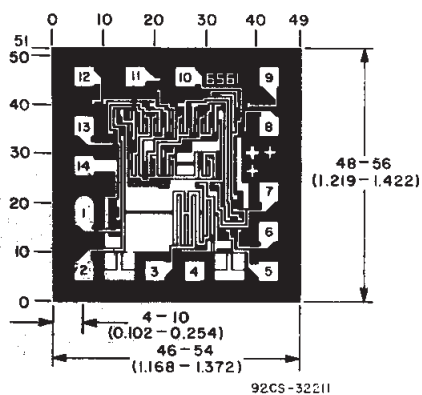


Fig. 15 - Input voltage.



Dimensions in parentheses are in millimeters and are derived from the basic inch dimensions as indicated. Grid graduations are in mils ( $10^{-3}$  inch).

## Dimensions and Pad Layout for the CD4086BH

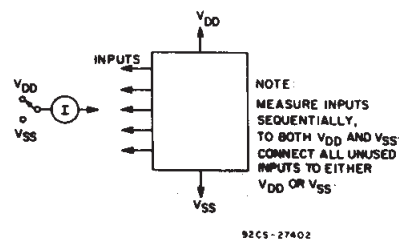


Fig. 16 - Input leakage current.

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